

NCE P-Channel Super Trench Power MOSFET

Description

The NCEP40P60Q uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification

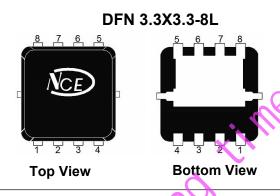
Application

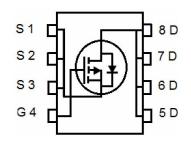
- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

General Features

- V_{DS} =-40V, I_D =-60A $R_{DS(ON)}$ =8.8m Ω (typical) @ V_{GS} =-10V $R_{DS(ON)}$ =12.5m Ω (typical) @ V_{GS} =-4.5V
- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 150 °C operating temperature
- Pb-free lead plating

100% UIS TESTED! 100% ΔVds TESTED!





Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP40P60Q	NCEP40P60Q	DFN3.3X3.3-8L	-	-	-

Absolute Maximum Ratings (T_c=25 ℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	-40	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	I _D (T _C =25℃)	-60	А
Drain Current-Continuous(T _C =100 °C)	I _D (T _C =100°C)	-42	Α
Pulsed Drain Current	I _{DM}	-240	Α
Maximum Power Dissipation(T _C =25 ℃)	P _D (T _C =25℃)	75	W
Derating factor		0.6	W/℃
Single pulse avalanche energy (Note 1)	E _{AS}	352	mJ
Operating Junction and Storage Temperature Range	T_{J},T_{STG}	-55 To 150	$^{\circ}$

Thermal Characteristic

Thermal Resistance, Junction-to-Case	ReJC	1.67	°C/W



NCEP40P60Q

Electrical Characteristics (T_C=25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics			•			
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250µA	-40		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-40V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics			•			
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =-250μA	-1.0	-1.7	-2.5	V
Drain Source On State Registence		V _{GS} =-10V, I _D =-20A	-	8.8	11.0	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-20A	-	12.5	17.0	mΩ
Forward Transconductance	g FS	V _{DS} =-5V,I _D =-20A	1	30	-	S
Dynamic Characteristics						
Input Capacitance	C _{iss}	V 20VVV 0V	-	2450	-	PF
Output Capacitance	Coss	V _{DS} =-20V,V _{GS} =0V,	-	660	-	PF
Reverse Transfer Capacitance	Crss	F=1.0MHz	-	18	-	PF
Switching Characteristics (Note 2)	'	119				
Turn-on Delay Time	t _{d(on)}		-	9	-	nS
Turn-on Rise Time	t _r	V _{DD} =-20V,I _D =-20A	-	4	-	nS
Turn-Off Delay Time	t _{d(off)}	V _{GS} =-10V,R _G =1.6Ω	-	30	-	nS
Turn-Off Fall Time	t _f		-	5	-	nS
Total Gate Charge	Qq	V 00V/1 00A	-	39	-	nC
Gate-Source Charge	Q _{gs}	V_{DS} =-20V, I_{D} =-20A, V_{GS} =-10V	-	7.8		nC
Gate-Drain Charge	Q_{gd}	V _{GS} =-10V	-	5.3		nC
Drain-Source Diode Characteristics	/					
Diode Forward Voltage	V _{SD}	V _{GS} =0V,I _S =-20A	-		-1.2	V
Diode Forward Current	Is		-	-	-60	Α
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F =-20A	-	22		nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs	-	58		nC

Notes:

- 1. EAS condition : Tj=25 $^{\circ}\mathrm{C}$,V_DD=-20V,V_G=-10V,L=0.5mH,Rg=25 Ω
- 2. Guaranteed by design, not subject to production
- 3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of TJ(MAX)=150°C. The SOA curve provides a single pulse rating.





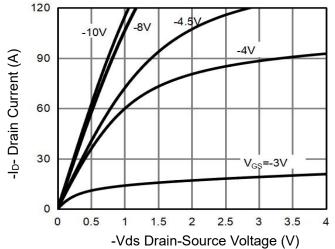


Figure 1 Output Characteristics

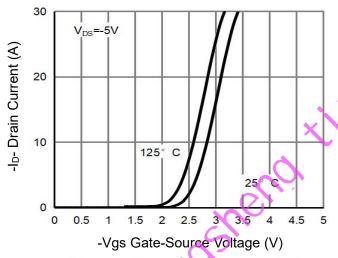
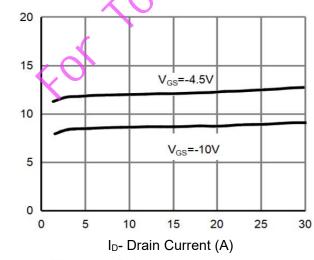


Figure 2 Transfer Characteristics



Rdson On-Resistance(m \(\Omega \))

Figure 3 Rdson- Drain Current

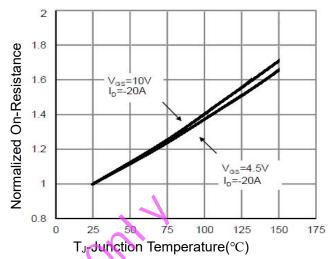


Figure 4 Rdson-JunctionTemperature

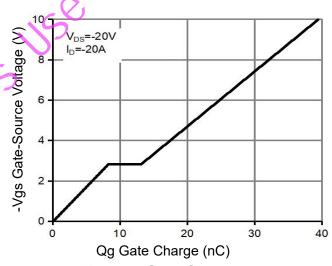


Figure 5 Gate Charge

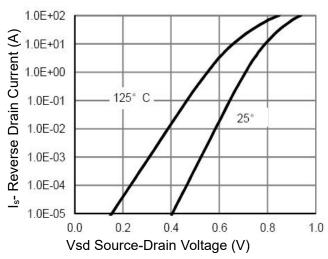
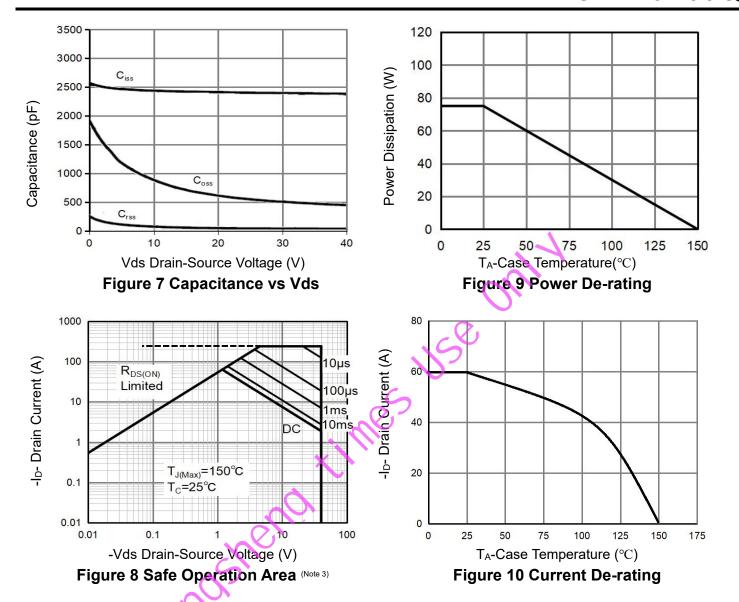


Figure 6 Source- Drain Diode Forward





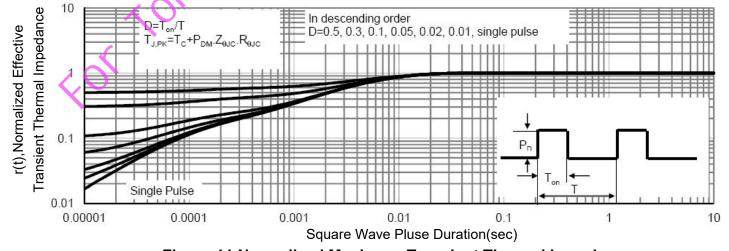
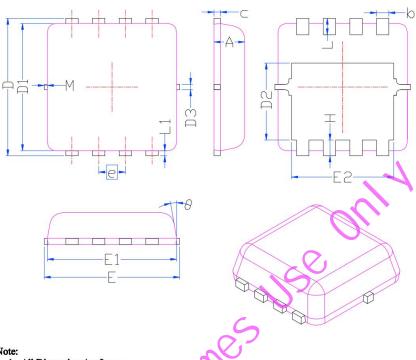


Figure 11 Normalized Maximum Transient Thermal Impedance



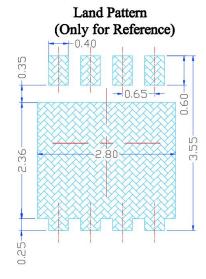
DFN3.3X3.3-8L Package Information



- Note:
 - 1. All Dimension Are In mm.

 - Package Body Sizes Exclude Mold Flash, Prorusion Or Gate Burrs.
 Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
 Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Tie Bar Burrs, Gate Burrs And Interlead Flash, But Including Any Mismatch Petween The Top And Bottom Of The Plastic Body.

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SYMBOL	MIN	NOM	MAX	
A	0.70	0.75	0.80	
b	0.25	0.30	0.35	
c	0.10	0.15	0.25	
D	3.25	3.35	3.45	
D1	3.00	3.10	3.20	
D2	1.78	1.88	1.98	
D3		0.13		
E	3.10	3.20	3.30	
E1	3.00	3.15	3.20	
E2	2.39	2.49	2.59	
e	0.65BSC			
Н	0.30	0.39	0.50	
L	0.30	0.40	0.50	
L1		0.13		
θ		10°	12°	
M	*	*	0.15	
* Not s	pecified	•		





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